

Si4463DY

P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

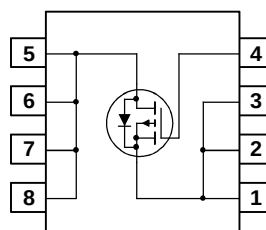
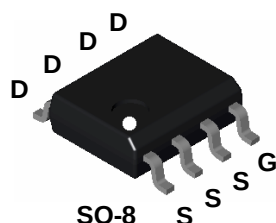
This P-Channel 2.5V specified MOSFET uses a rugged gate PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

Applications

- Power management
- Load switch
- Battery protection

Features

- –11.5 A, –20 V. $R_{DS(ON)} = 12\text{ m}\Omega$ @ $V_{GS} = -4.5\text{ V}$
 $R_{DS(ON)} = 17.5\text{ m}\Omega$ @ $V_{GS} = -2.5\text{ V}$
- Fast switching speed.
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	–20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Drain Current – Continuous (Note 1a)	–11.5	A
	– Pulsed	–50	
P_D	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
4463	Si4463DY	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		-12		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.6	-0.8	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C		3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -11.5\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -9.5\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -11.5\text{ A}, T_J = 125^\circ\text{C}$		10 14 13	12 17.5 18	m Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-50			A
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -10\text{ A}$		49		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		4481		pF
C_{oss}	Output Capacitance			1532		pF
C_{rss}	Reverse Transfer Capacitance			540		pF

Switching Characteristics (Note 2)

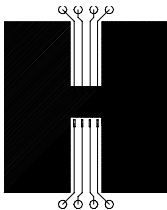
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -5\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\text{ }\Omega$		15	30	ns
t_r	Turn–On Rise Time			15	30	ns
$t_{d(off)}$	Turn–Off Delay Time			120	240	ns
t_f	Turn–Off Fall Time			60	120	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -11.5\text{ A},$ $V_{GS} = -4.5\text{ V}$		41	60	nC
Q_{gs}	Gate–Source Charge			6.4		nC
Q_{gd}	Gate–Drain Charge			11.8		nC

Drain–Source Diode Characteristics and Maximum Ratings

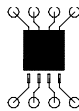
I_S	Maximum Continuous Drain–Source Diode Forward Current			-2.1		A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.5\text{ A}$ (Note 2)		-0.65	-1.2	V

Notes:

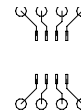
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°W when mounted on a 1 in^2 pad of 2 oz copper



b) 105°W when mounted on a $.04\text{ in}^2$ pad of 2 oz copper



c) 125°W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

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